

# MSKSEMI 美森科

SEMICONDUCTOR



ESD



TVS



TSS



MOV



GDT



PLED

**1SMA59XXBT3G-MS**

**Product specification**

**Features**

- Standard Zener Breakdown Voltage Range – 3.3 V to 68 V
- ESD Rating of Class 3 (> 16 kV) per Human Body Model
- Flat Handling Surface for Accurate Placement
- Package Design for Top Side or Bottom Circuit Board Mounting
- Low Profile Package
- Ideal Replacement for MELF Packages

**Mechanical Characteristics:**

**CASE:** Void-free, transfer-molded plastic

**FINISH:** All external surfaces are corrosion resistant with readily solderable leads

**MAXIMUM CASE TEMPERATURE FOR SOLDERING PURPOSES:**

260°C for 10 seconds

**POLARITY:** Cathode indicated by molded polarity notch or cathode band

**FLAMMABILITY RATING:** UL 94 V-0 @ 0.125 in


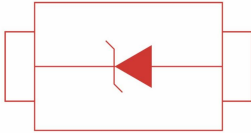
**MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
DC Power Dissipation @ TL = 75°C, Measured Zero Lead Length (Note 1) Derate above 75°C Thermal Resistance, Junction-to-Lead	PD  RθJL	1.5 20 50	W mW/°C °C/W
DC Power Dissipation @ TA = 25°C (Note 2) Derate above 25°C Thermal Resistance, Junction-to-Ambient	PD  RθJA	0.5 4.0 250	W mW/°C °C/W
Operating and Storage Temperature Range	TJ, Tstg	-65 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

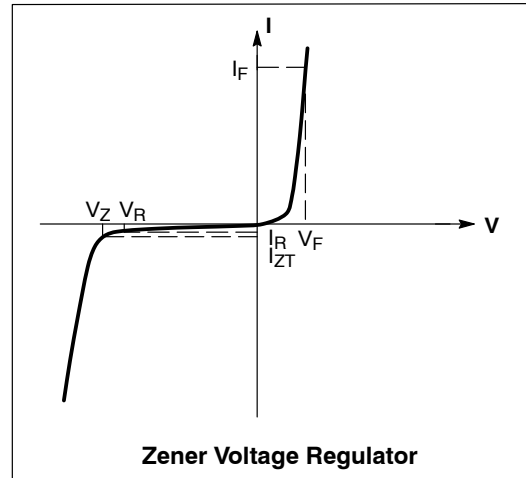
1. 1 in square copper pad, FR-4 board.
2. FR-4 Board, using **onsemi** minimum recommended footprint.

**Reference News**

PACKAGE OUTLINE	PIN CONFIGURATION
	
SMA(DO-214AC)	

**ELECTRICAL CHARACTERISTICS** (TA = 25°C  
unless otherwise noted, VF = 1.2 V Max. @ IF = 200  
mA for all types)

Symbol	Parameter
Vz	Reverse Zener Voltage @ IZT
IZT	Reverse Current
ZzT	Maximum Zener Impedance @ IZT
IZK	Reverse Current
ZzK	Maximum Zener Impedance @ IZK
IR	Reverse Leakage Current @ VR
VR	Reverse Voltage
IF	Forward Current
VF	Forward Voltage @ IF
IZM	Maximum DC Zener Current



**ELECTRICAL CHARACTERISTICS** (TA = 25°C unless otherwise noted, VF = 1.2 V Max. @ IF = 200 mA for all types)

Device* (Note 3)	Device Marking	Zener Voltage (Note 4)				Zener Impedance			Leakage Current		IZM
		Vz(Volts)			@ IZT	ZzT @ IZT	Zzk @ IZK	IR @ VR			
		Min	Nom	Max	mA	Ω	Ω	mA	μA	Volts	
1SMA5913BT3G-MS	MSKSEMI 813B	3.13	3.3	3.47	113.6	10	500	1.0	50	1.0	455
1SMA5914BT3G-MS	MSKSEMI 814B	3.42	3.6	3.78	104.2	9.0	500	1.0	35.5	1.0	417
1SMA5915BT3G-MS	MSKSEMI 815B	3.70	3.9	4.10	96.1	7.5	500	1.0	12.5	1.0	385
1SMA5916BT3G-MS	MSKSEMI 816B	4.08	4.3	4.52	87.2	6.0	500	1.0	2.5	1.0	349
1SMA5917BT3G-MS	MSKSEMI 817B	4.46	4.7	4.94	79.8	5.0	500	1.0	2.5	1.5	319
1SMA5918BT3G-MS	MSKSEMI 818B	4.84	5.1	5.36	73.5	4.0	350	1.0	2.5	2.0	294
1SMA5919BT3G-MS	MSKSEMI 819B	5.32	5.6	5.88	66.9	2.0	250	1.0	2.5	3.0	268
1SMA5920BT3G-MS	MSKSEMI 820B	5.89	6.2	6.51	60.5	2.0	200	1.0	2.5	4.0	242
1SMA5921BT3G-MS	MSKSEMI 821B	6.46	6.8	7.14	55.1	2.5	200	1.0	2.5	5.2	221
1SMA5922BT3G-MS	MSKSEMI 822B	7.12	7.5	7.88	50	3.0	400	0.5	2.5	6.0	200
1SMA5923BT3G-MS	MSKSEMI 823B	7.79	8.2	8.61	45.7	3.5	400	0.5	2.5	6.5	183
1SMA5924BT3G-MS	MSKSEMI 824B	8.64	9.1	9.56	41.2	4.0	500	0.5	2.5	7.0	165
1SMA5925BT3G-MS	MSKSEMI 825B	9.5	10	10.5	37.5	4.5	500	0.25	2.5	8.0	150
1SMA5926BT3G-MS	MSKSEMI 826B	10.45	11	11.55	34.1	5.5	550	0.25	0.5	8.4	136
1SMA5927BT3G-MS	MSKSEMI 827B	11.4	12	12.6	31.2	6.5	550	0.25	0.5	9.1	125
1SMA5928BT3G-MS	MSKSEMI 828B	12.35	13	13.65	28.8	7.0	550	0.25	0.5	9.9	115
1SMA5929BT3G-MS	MSKSEMI 829B	14.25	15	15.75	25	9.0	600	0.25	0.5	11.4	100
1SMA5930BT3G-MS	MSKSEMI 830B	15.2	16	16.8	23.4	10	600	0.25	0.5	12.2	94
1SMA5931BT3G-MS	MSKSEMI 831B	17.1	18	18.9	20.8	12	650	0.25	0.5	13.7	83
1SMA5932BT3G-MS	MSKSEMI 832B	19	20	21	18.7	14	650	0.25	0.5	15.2	75
1SMA5933BT3G-MS	MSKSEMI 833B	20.9	22	23.1	17	17.5	650	0.25	0.5	16.7	68
1SMA5934BT3G-MS	MSKSEMI 834B	22.8	24	25.2	15.6	19	700	0.25	0.5	18.2	63
1SMA5935BT3G-MS	MSKSEMI 835B	25.65	27	28.35	13.9	23	700	0.25	0.5	20.6	56
1SMA5936BT3G-MS	MSKSEMI 836B	28.5	30	31.5	12.5	26	750	0.25	0.5	22.8	50
1SMA5937BT3G-MS	MSKSEMI 837B	31.35	33	34.65	11.4	33	800	0.25	0.5	25.1	45
1SMA5938BT3G-MS	MSKSEMI 838B	34.2	36	37.8	10.4	38	850	0.25	0.5	27.4	42
1SMA5939BT3G-MS	MSKSEMI 839B	37.05	39	40.95	9.6	45	900	0.25	0.5	29.7	38
1SMA5940BT3G-MS	MSKSEMI 840B	40.85	43	45.15	8.7	53	950	0.25	0.5	32.7	35
1SMA5941BT3G-MS	MSKSEMI 841B	44.65	47	49.35	8.0	67	1000	0.25	0.5	35.8	32
1SMA5942BT3G-MS	MSKSEMI 842B	48.45	51	53.55	7.3	70	1100	0.25	0.5	38.8	29
1SMA5943BT3G-MS	MSKSEMI 843B	53.2	56	58.8	6.7	86	1300	0.25	0.5	42.6	27
1SMA5945BT3G-MS	MSKSEMI 845B	64.6	68	71.4	5.5	120	1700	0.25	0.5	51.7	22

3. Tolerance and Voltage Regulation Designation – The type number listed indicates a tolerance of ±5%.

4. Vz limits are to be guaranteed at thermal equilibrium.

RATING AND TYPICAL CHARACTERISTIC CURVES (TA = 25°C)

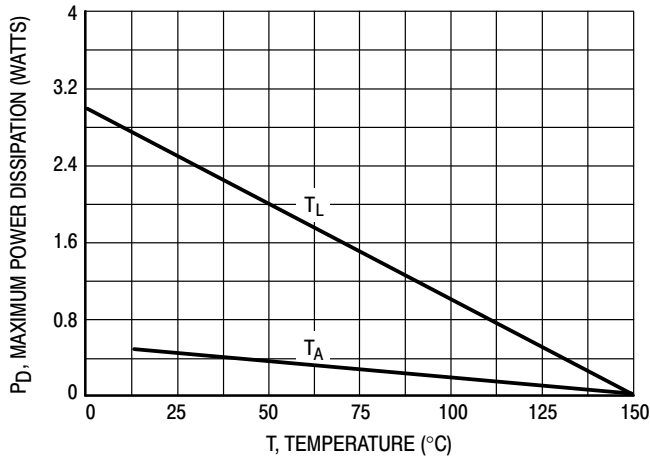


Figure 1. Steady State Power Derating

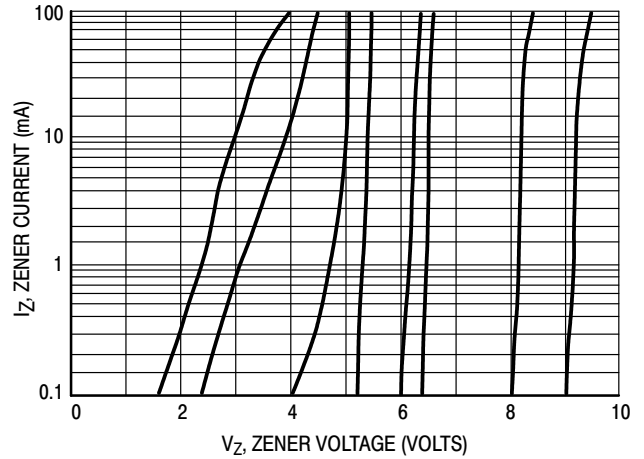


Figure 2. V<sub>Z</sub> – 3.3 thru 10 Volts

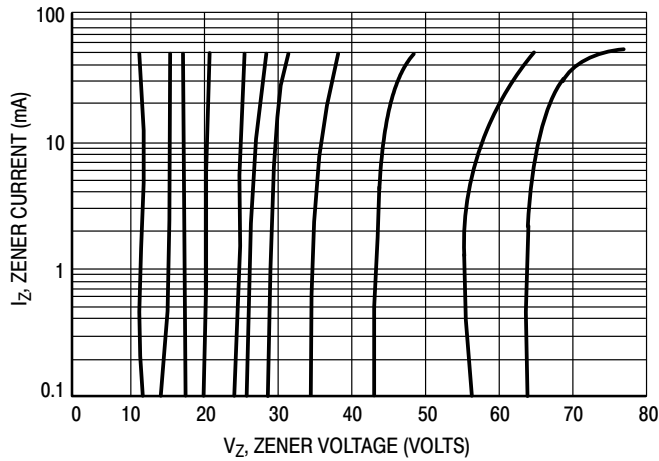


Figure 3. V<sub>Z</sub> = 12 thru 68 Volts

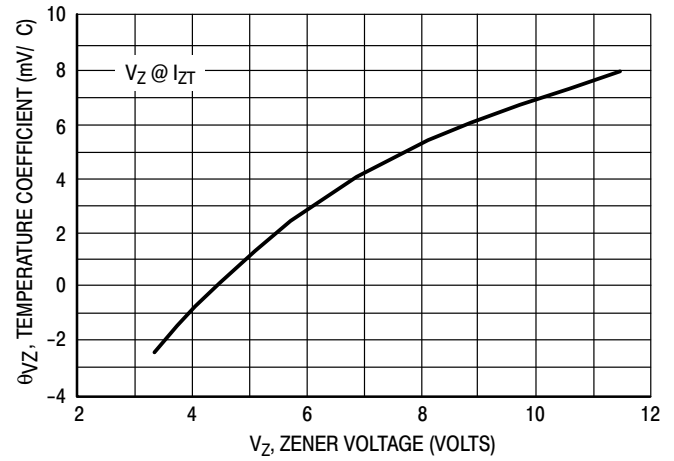


Figure 4. Zener Voltage – 3.3 to 12 Volts

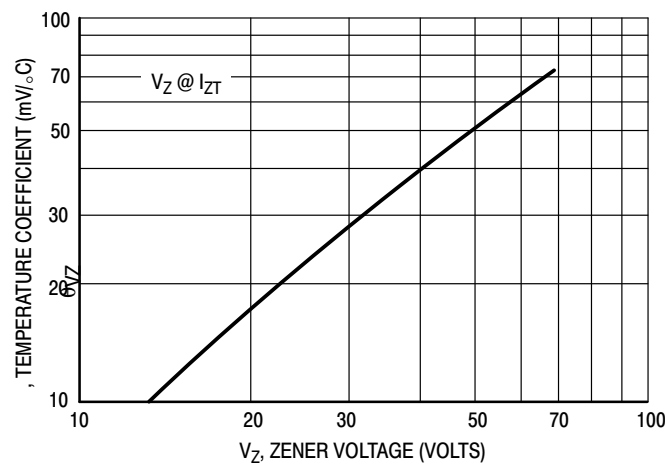


Figure 5. Zener Voltage – 12 to 68 Volts

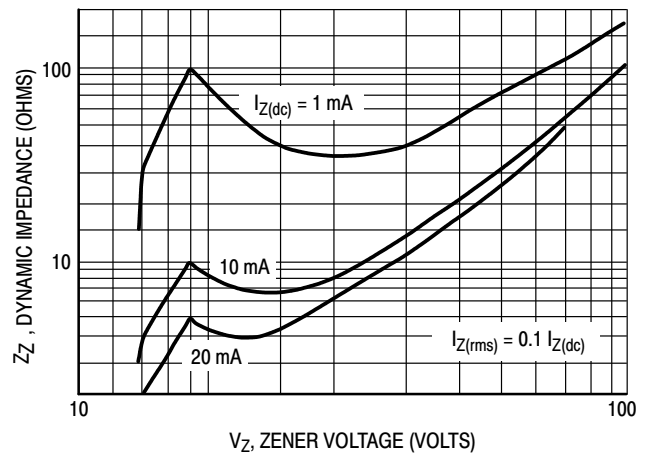
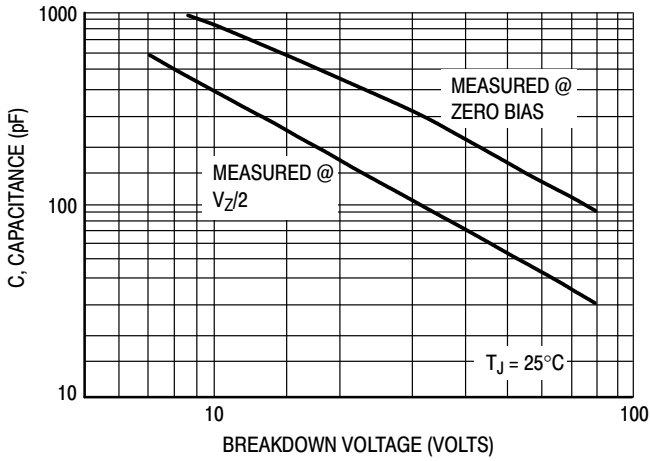
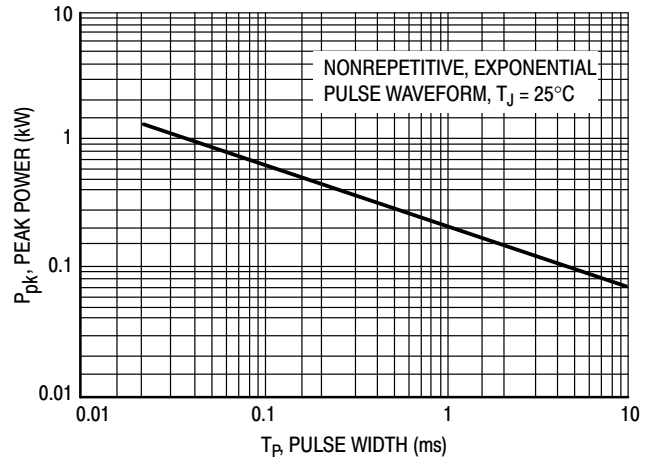


Figure 6. Effect of Zener Voltage

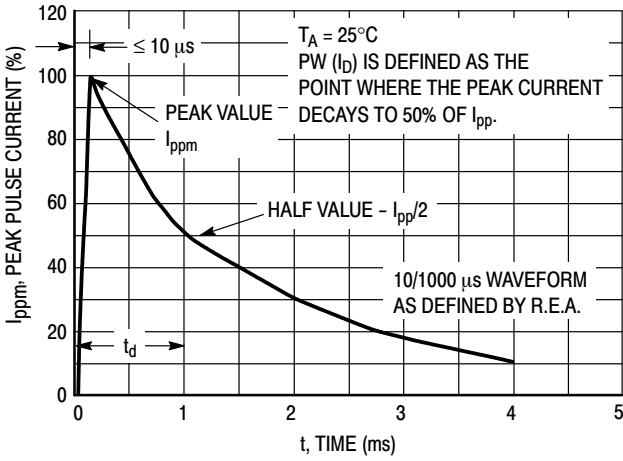
**RATING AND TYPICAL CHARACTERISTIC CURVES (TA = 25°C)**



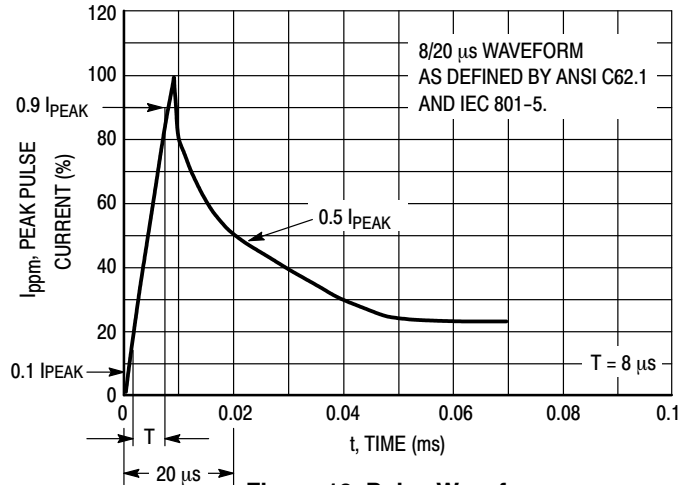
**Figure 7. Capacitance Curve**



**Figure 8. Typical Pulse Rating Curve**

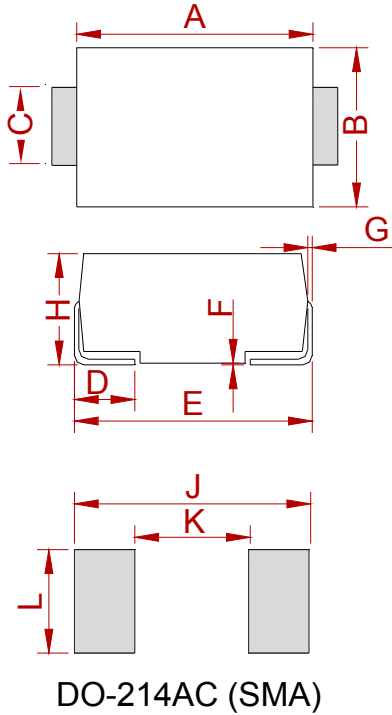


**Figure 9. Pulse Waveform**



**Figure 10. Pulse Waveform**

**PACKAGE MECHANICAL DATA**



Ref.	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.25	4.65	0.167	0.183
B	2.50	2.90	0.098	0.114
C	1.35	1.65	0.053	0.065
D	0.76	1.52	0.030	0.060
E	4.93	5.28	0.194	0.208
F	0.051	0.203	0.002	0.008
G	0.15	0.31	0.006	0.012
H	1.98	2.41	0.078	0.095
J	6.50		0.256	
K		2.30		0.090
L	1.70		0.067	

**REEL SPECIFICATION**

P/N	PKG	QTY
1SMA59XXBT3G-MS	SMA	2000

## Attention

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